

S200 - 50

200 Watts, 50 Volts, Class AB Milcom 1.5 - 30 MHz

GENERAL DESCRIPTION

The S200-50 is a COMMON EMITTER, HF, SSB device intended for operation from a 50 Volts supply. It may be operated in Class A, AB or C. The device exhibits excellent linearity and ruggedness.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 320 Watts

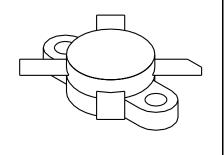
Maximum Voltage and Current

BVces Collector to Emiter Voltage 100 Volts
BVebo Emitter to Base Voltage 4.0 Volts
Ic Collector Current 30 A

Maximum Temperatures

Storage Temperature $-65 \text{ to } +150^{\circ}\text{C}$ Operating Junction Temperature $+150^{\circ}\text{C}$

CASE OUTLINE 55HX, Style 2



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg ηc VSWR	Power Output Power Input Power Gain Efficiency Load Mismatch Tolerance	F = 30 MHz Vcc = 50 Volts	200 12	14.5 60	12 30:1	Watts Watts dB %

Initial Issue June, 1994

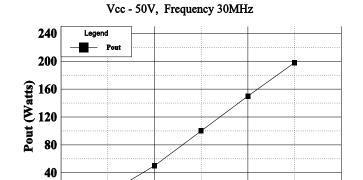
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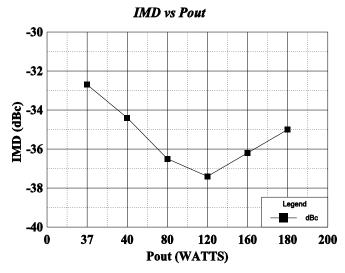
DC SAFE OPERATING AREA

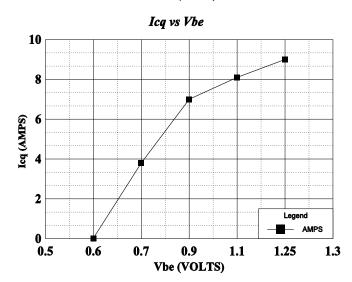
POWER OUTPUT vs POWER INPUT



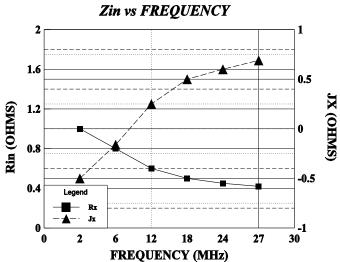
7.5

8





Pin (Watts)

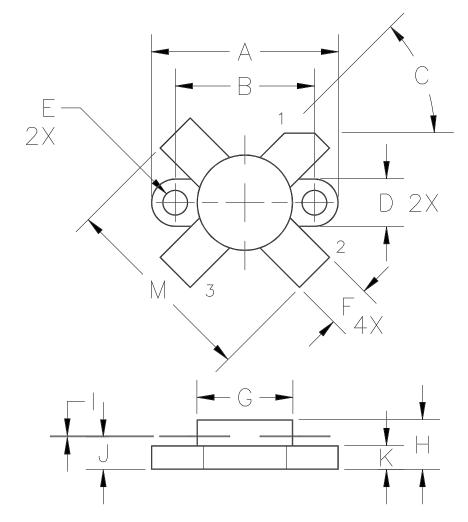


0

0.8

2





DIM	MILLIMETER	TOL	INCHES	TOL
Α	24.76	.13	.975	.005
В	18.42	.13	.725	.005
С	45°	5°	45°	5°
D	6.35	.13	.250	.005
Е	3.17 DIA	.13	.125 DIA	.005
F	5.71	.13	.225	.005
G	12.70	.13	.500 DIA	.005
Н	6.60	REF	.260	REF
	0.13	.02	.005	.001
J	4.32	.18	.170	.007
K	3.17	.25	.125	.010
М	26.16	.25	1.030	.010

STYLE 1:

PIN1 = COLLECTOR2 = BASE (2X)

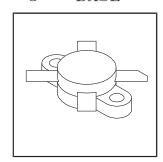
3 = EMITTER

STYLE 2:

PIN1 = COLLECTOR

2 = EMITTER (2X)

3 = BASE





GHz	TEC	HNO	LOGY

cage	DWG NO.	55HX		REV A	
	SCALE	2/1	SHEET		